

# HiPerFET™

## Power MOSFETs

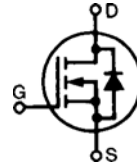
### Q Class

IXFH/IXFT12N100Q  
IXFH/IXFT10N100Q

$V_{DSS}$	$I_{D25}$	$R_{DS(on)}$
1000 V	12 A	1.05 $\Omega$
1000 V	10 A	1.20 $\Omega$

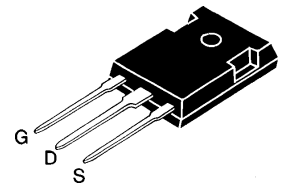
$t_{rr} \leq 250$  ns

N-Channel Enhancement Mode  
Avalanche Rated  
Low  $Q_g$ , High  $dv/dt$

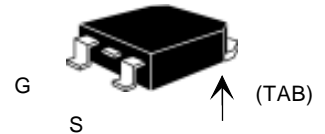


Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	1000	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1\text{ M}\Omega$	1000	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	12N100Q	12 A
		10N100Q	10 A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	12N100Q	48 A
		10N100Q	40 A
$I_{AR}$	$T_C = 25^\circ\text{C}$	12N100Q	12 A
		10N100Q	10 A
$E_{AR}$	$T_C = 25^\circ\text{C}$	30	mJ
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100\text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 2\ \Omega$	5	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	300	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
$M_d$	Mounting torque	1.13/10	Nm/lb.in.
Weight		TO-247 AD	6 g
		TO-268	4 g

TO-247 AD (IXFH)



TO-268 (D3) (IXFT)



G = Gate      D = Drain  
S = Source    TAB = Drain

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = 3\text{ mA}$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4\text{ mA}$	2.5		5.5 V
$I_{GSS}$	$V_{GS} = \pm 20\text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = 0.8 \cdot V_{DSS}$ $V_{GS} = 0\text{ V}$	$T_J = 25^\circ\text{C}$		50 $\mu\text{A}$
		$T_J = 125^\circ\text{C}$		1 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$	12N100Q		1.05 $\Omega$
		10N100Q		1.20 $\Omega$

#### Features

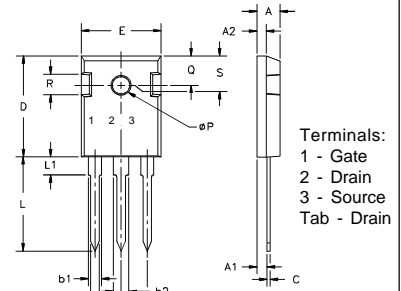
- IXYS advanced low  $Q_g$  process
- Low gate charge and capacitances
  - easier to drive
  - faster switching
- International standard packages
- Low  $R_{DS(on)}$
- Unclamped Inductive Switching (UIS) rated
- Molding epoxies meet UL 94 V-0 flammability classification

#### Advantages

- Easy to mount
- Space savings
- High power density

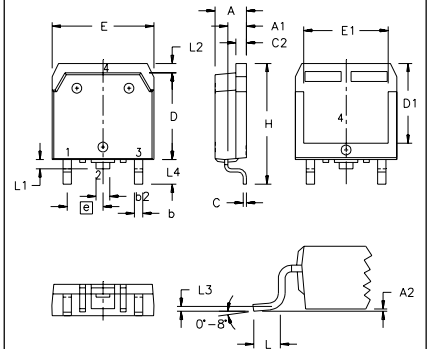
Symbol	Test Conditions	Characteristic Values ( $T_j = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$V_{DS} = 15\text{ V}; I_D = 0.5 \cdot I_{D25}$ , pulse test	4	10	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		2900	pF
$C_{oss}$			315	pF
$C_{rss}$			50	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 2\ \Omega$ (External),		20	ns
$t_r$			23	ns
$t_{d(off)}$			40	ns
$t_f$			15	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		90	nC
$Q_{gs}$			30	nC
$Q_{gd}$			40	nC
$R_{thJC}$	(TO-247)			0.42 K/W
$R_{thCK}$			0.25	K/W

Source-Drain Diode		Characteristic Values ( $T_j = 25^\circ\text{C}$ , unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
$I_S$	$V_{GS} = 0\text{ V}$			12 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$			48 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		200	ns
$Q_{RM}$			0.6	$\mu\text{C}$
$I_{RM}$			7	A

**TO-247 AD (IXFH) Outline**


Terminals:  
 1 - Gate  
 2 - Drain  
 3 - Source  
 Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.087	.102
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

**TO-268 Outline**


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	54.3	55.1	13.80	14.00
D1	48.8	50.0	12.40	12.70
E	62.4	63.2	15.85	16.05
E1	52.4	53.5	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

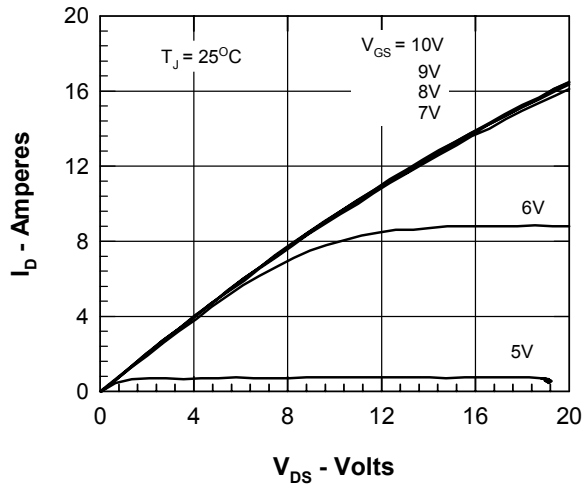


Figure 1. Output Characteristics at 25°C

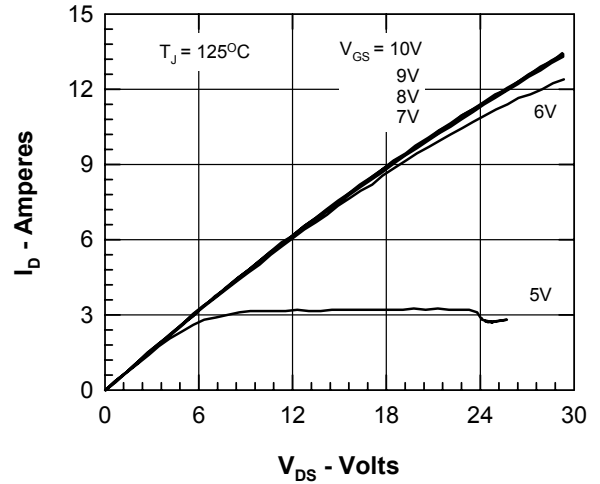


Figure 2. Output Characteristics at 125°C

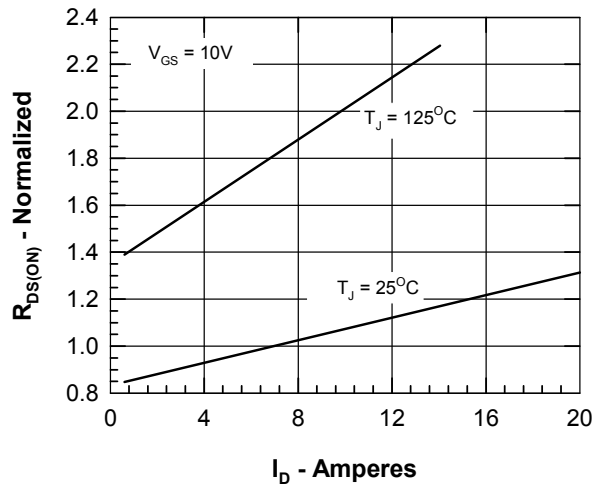


Figure 3.  $R_{DS(on)}$  normalized to value at  $I_D = 12A$

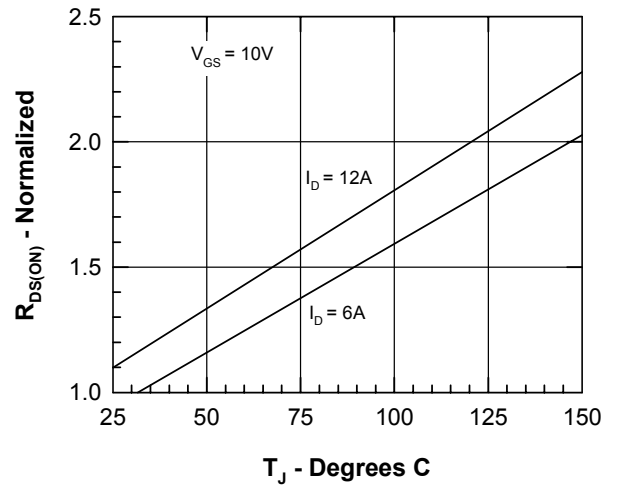


Figure 4.  $R_{DS(on)}$  normalized to value at  $I_D = 12A$

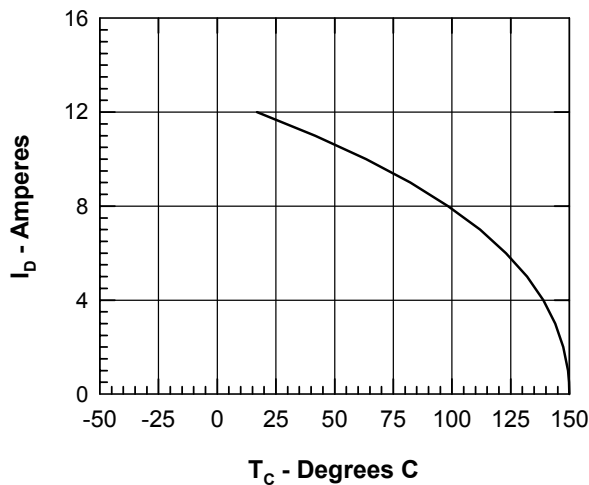


Figure 5. Drain Current vs. Case Temperature

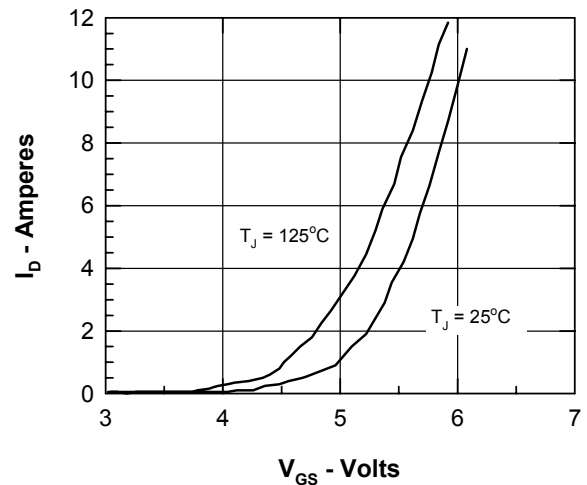


Figure 6. Admittance Curves

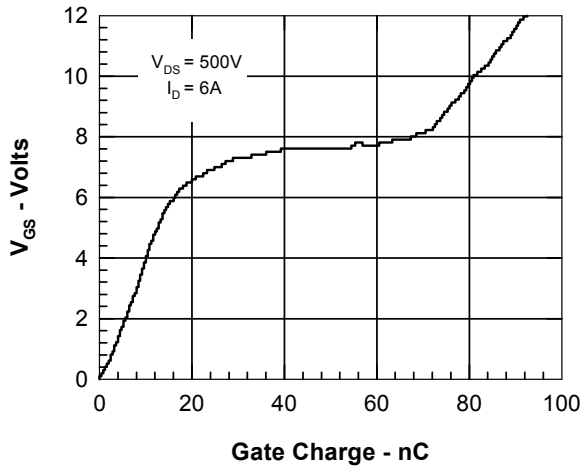


Figure 7. Gate Charge

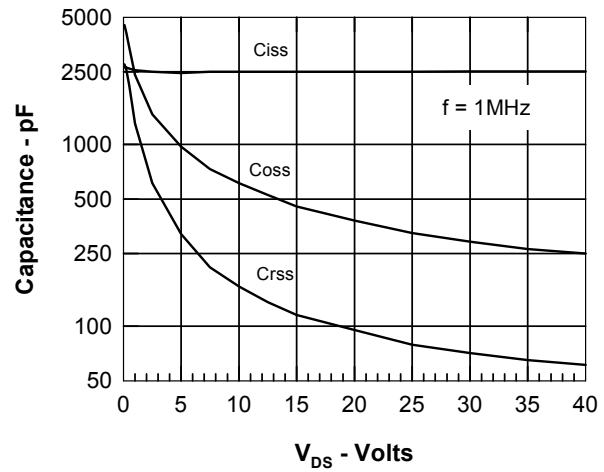


Figure 8. Capacitance Curves

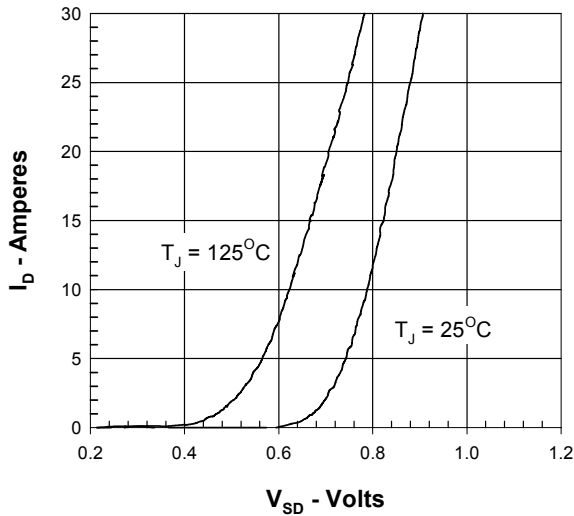


Figure 9. Source Current vs. Source to Drain Voltage

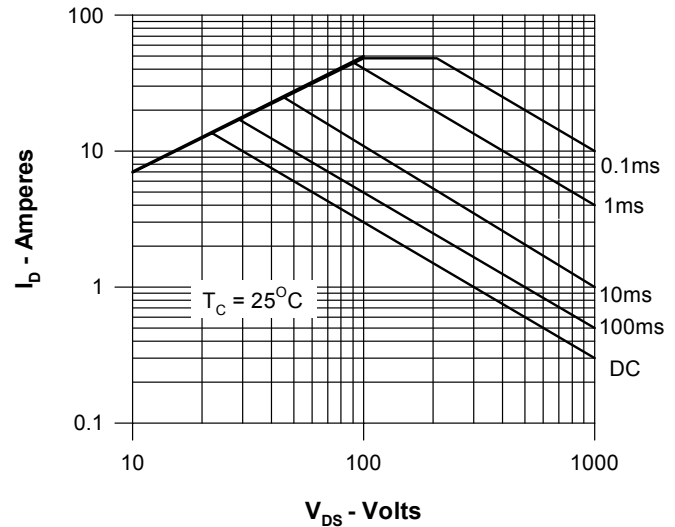


Figure 10. Forward Bias Safe Operating Area

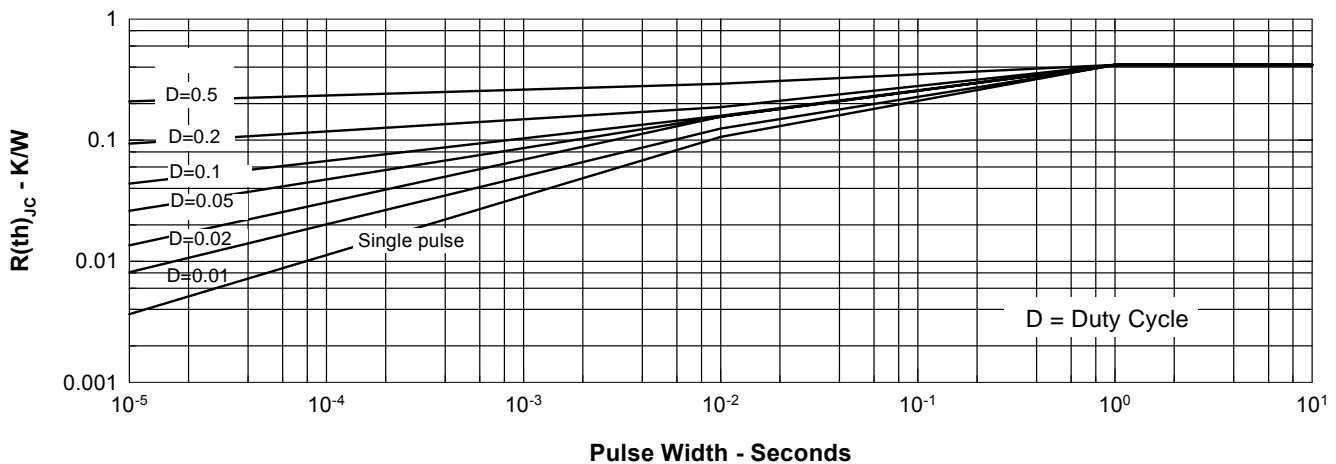


Figure 11. Transient Thermal Resistance

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
	4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	